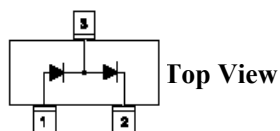


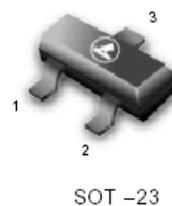


Dual In-Series Small-Signal Switching Diode

- Silicon Epitaxial Planar Diode
- Fast switching dual in-series diode, especially suited for applications requiring high voltage capability



LSD2004SLT1



Driver Marking

LSD2004SLT1 =DB6

Maximum Ratings and Thermal Characteristics

TA = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	VR	240	V
Peak Repetitive Reverse Voltage	VRRM	300	V
Peak Repetitive Reverse Current	IRRM	200	mA
Forward Current (continuous)	IF	225	mA
Peak Repetitive Forward Current	IRFM	625	mA
Non-Repetitive Peak Forward Current			
at tp = 1μs	IFSM	4	A
at tp = 1s		1	
Power Dissipation	Ptot	350	mW
Typical Thermal Resistance Junction to Ambient Air	RθJA	357	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature Range	TS	-65 to +150	°C



LESHAN RADIO COMPANY, LTD.

LSD2004SLT1

Electrical Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R = 100\mu\text{A}$	300	—	—	V
Leakage Current	I_R	$V_R = 240\text{V}$	—	—	100	nA
		$V_R = 240\text{V}, T_J = 150^\circ\text{C}$	—	—	100	μA
Forward Voltage	V_F	$I_F = 20\text{mA}$	—	—	0.87	V
		$I_F = 100\text{mA}$	—	—	1	
Capacitance	C_{tot}	$V_F = V_R = 0$	—	—	5	pF
		$f = 1\text{MHz}$	—	—	—	
Reverse Recovery Time	t_{rr}	$I_F = I_A = 30\text{mA}$	—	—	50	ns
		$I_{rr} = 30\text{mA}, R_L = 100\Omega$	—	—	—	

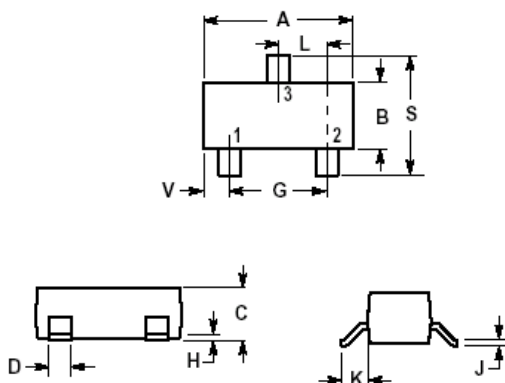
SOT-23

NOTES:

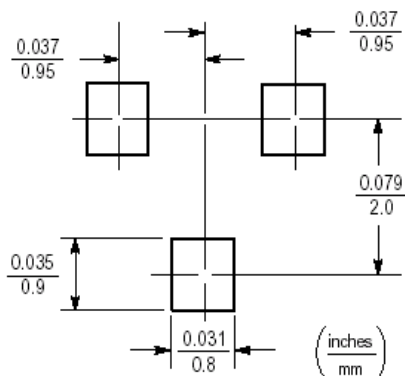
1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982

2. CONTROLLING DIMENSION: INCH



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60



LSD2004SLT1—2/2